16. (Thrice Amended) A semiconductor structure comprising:

a semiconductor substrate; and

C1 an antireflective coating over the semiconductor substrate, the antireflective coating comprising a metal silicon nitride compound, the metal being at least one metal selected from the group consisting of Sc, Co, and Ni, wherein the antireflective coating is configured to minimize reflectivity of deep ultraviolet light.

26. (Thrice Amended) A semiconductor structure comprising:

C2 a semiconductor substrate; and

an antireflective coating upon said semiconductor substrate, the antireflective coating comprising a metal silicon nitride compound $M_xSi_yN_z$, wherein:

x is greater than zero;

y is greater than x;

z is greater than zero and less than about 5y;

M is at least two transition metals $M1_rM2_{1-r}$;

r is in a range from 0 to 1;

M1 and M2 are selected from the group consisting of Sc, Zr, Nb, Ta, Mo, Co, Al, and Ni; and

M1 is not M2.

29. (Thrice Amended) A semiconductor structure comprising:

an electrically insulative layer upon a semiconductor substrate;

a patterned electrically conductive metal line upon the electrically insulative layer; and

C13

an antireflective coating upon said electrically conductive metal line, wherein the antireflective coating is configured to minimize reflectivity of deep ultraviolet light, the antireflective coating comprising a metal silicon nitride compound $M_xSi_yN_z$, wherein:

x is greater than zero;

M is at least one transition metal selected from the group consisting of Sc, Co, and Ni;

y is greater than x; and

z is greater than about 0 and less than about 5y.

42. (Once Amended) A semiconductor structure comprising:

C14

a semiconductor substrate; and

an antireflective coating over the semiconductor substrate, the antireflective coating comprising a metal silicon nitride compound, wherein the metal is at least one metal selected from the group consisting of Sc, Co, and Ni.

43. (Twice Amended) A semiconductor structure comprising:

a semiconductor substrate; and

C5

an antireflective coating over the semiconductor substrate and having a thickness range from about 25 Angstroms to about 200 Angstroms, the antireflective coating comprising a metal silicon nitride compound, wherein the metal is at least one metal selected from the group consisting of Sc, Co, and Ni.